

## Product Overview

### NSBC114EDXV6: Dual NPN Bipolar Digital Transistor (BRT)

For complete documentation, see the data sheet.

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

### Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### Part Electrical Specifications

Product	Compliance	Status	Polarity	$I_C$ Continuous (A)	$V_{BRICE0}$ Min (V)	$h_{FE}$ Min	R1 (k $\Omega$ )	R2 (k $\Omega$ )	R1/R2 Typ	$V_{i(off)}$ Max (V)	$V_{i(on)}$ Min (V)	Package Type
NSBC114EDXV6T1G	Pb-free Halide free	Active	Dual NPN	0.1	50	35	10	10	1	0.8	2.5	SOT-563
NSBC114EDXV6T5G	Pb-free Halide free	Active	Dual NPN	0.1	50	35	10	10	1	0.8	2.5	SOT-563
NSVBC114EDXV6T1G	AEC Qualified PPAP Capable Pb-free Halide free	Active	Dual NPN	0.1	50	35	10	10	1	0.8	2.5	SOT-563

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